

ABSTRACT OF THE DISCLOSURE

- A method for manufacturing a semiconductor device comprises: forming an N region and P region on a substrate, forming wiring so as to connect one or both of these N and P regions; and performing a processing step on a semiconductor substrate on
- 5 which the upper surface of said wiring is exposed using a liquid, wherein said processing step is performed in a state in which the wavelength of light radiated onto said semiconductor substrate is 500 nm to less than 1 μ m, so that problems such as wiring connection defects for which there is the risk of occurring in the cleaning step are prevented by performing the cleaning step during, before or after a step that includes
- 10 chemical mechanical polishing (CMP) for forming the above wiring.